

Product Summary

Part #	V_{DS}	$R_{DS(on).typ}$ (@ $V_{GS}=10V$)	$R_{DS(on).typ}$ (@ $V_{GS}=4.5V$)	I_D
EFM3434A	30V	42m Ω	47m Ω	4A

Features

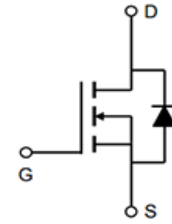
- Low $R_{DS(on)}$ @ $V_{GS}=10V$
- 4.5V Logic Level Control
- N Channel SOT23-3L Package
- Pb-Free, RoHS Compliant

Application

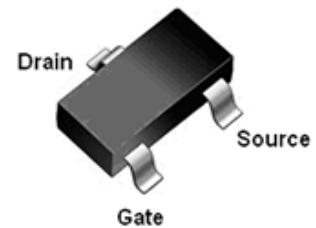
- DC-to-DC converters
- Power management in battery-driven portables
- Low-side load switch and charging switch for portable devices
- Switching circuits
- High-speed line driver

Ordering Information:

Part NO.	EFM3434A
Marking	Y4****
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000



N-Channel MOSFET



SOT23-3L



Absolute Maximum Ratings ($T_C=25^\circ C$)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	4	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	90	$^\circ C/W$
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• Static Electrical Characteristics @ $T_J = 25^{\circ}\text{C}$ (unless otherwise stated)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V$ $V_{GS}=0V$	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V$ $V_{DS}=0V$	--	--	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	0.5	0.8	1.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V$ $I_D=4A$	--	42	47	m Ω
		$V_{GS}=4.5V$ $I_D=3A$	--	47	60	m Ω
Dynamic Characteristics ^(Note4)						
Input Capacitance	C_{ISS}	$V_{DS}=15V$ $V_{GS}=0V$ $F=1.0MHz$	--	245	--	PF
Output Capacitance	C_{OSS}		--	35	--	PF
Reverse Transfer Capacitance	C_{RSS}		--	20	--	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V$ $I_D=4A$ $V_{GS}=10V$ $R_G=3\Omega$,	--	2	--	nS
Turn-on Rise Time	t_r		--	3.5	--	nS
Turn-Off Delay Time	$t_{d(off)}$		--	22	--	nS
Turn-Off Fall Time	t_f		--	3.5	--	nS
Total Gate Charge	Q_g	$V_{DS}=15V$ $I_D=4A$ $V_{GS}=10V$	--	5.7	--	nC
Gate-Source Charge	Q_{gs}		--	0.5	--	nC
Gate-Drain Charge	Q_{gd}		--	1.0	--	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V$ $I_S=4A$	--	0.75	1.0	V
Diode Forward Current ^(Note 2)	I_S		--	--	4	A

Notes:

- ① Pulse width limited by maximum allowable junction temperature
 ② Pulse test ; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

• Typical Characteristics

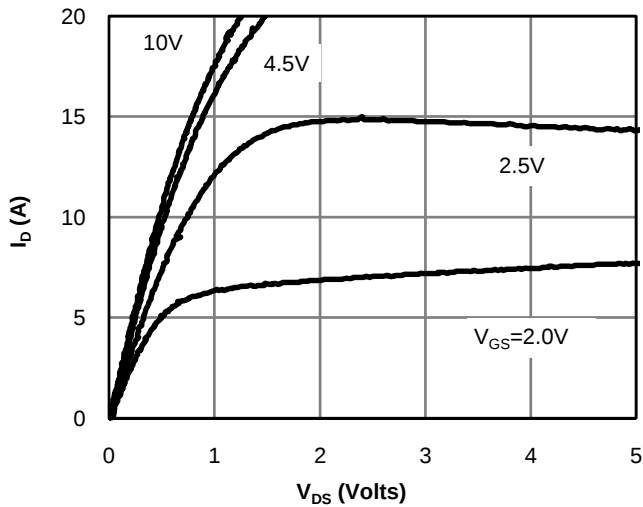


Fig 1: On-Region Characteristics (Note E)

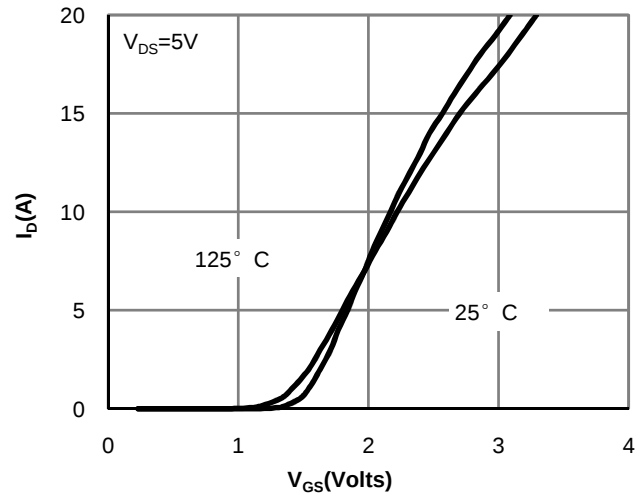


Figure 2: Transfer Characteristics (Note E)

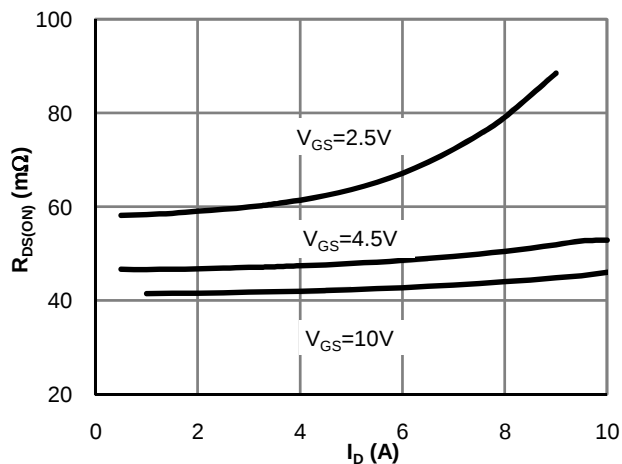


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

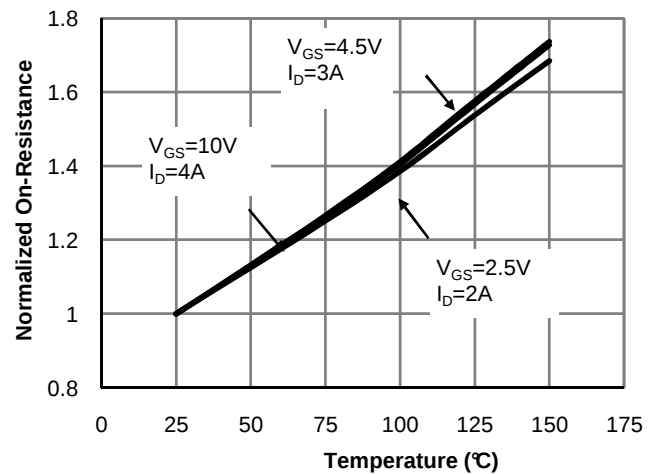


Figure 4: On-Resistance vs. Junction Temperature (Note E)

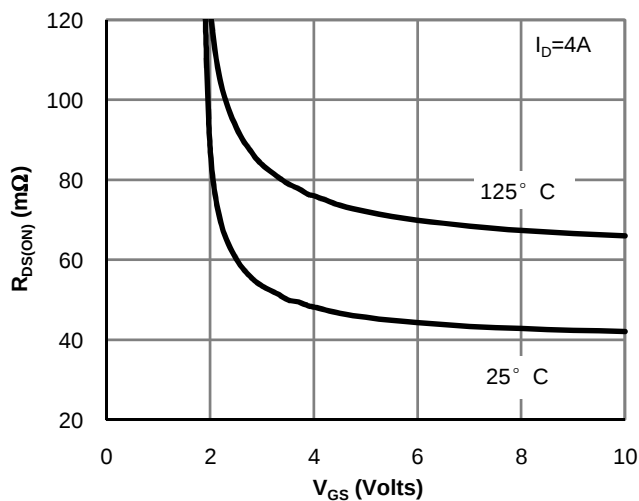


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

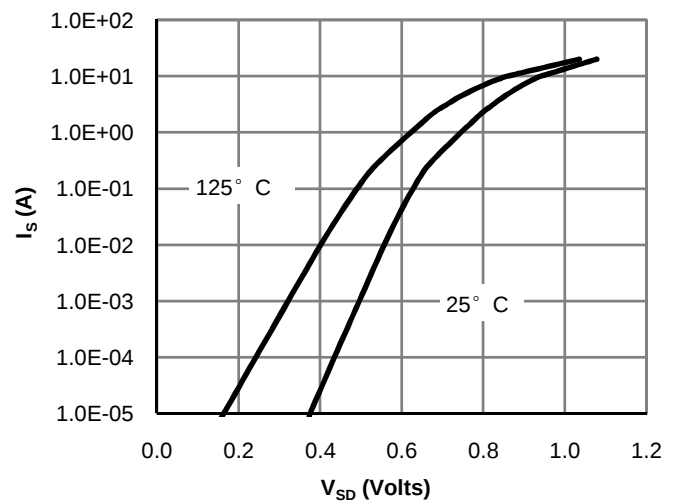
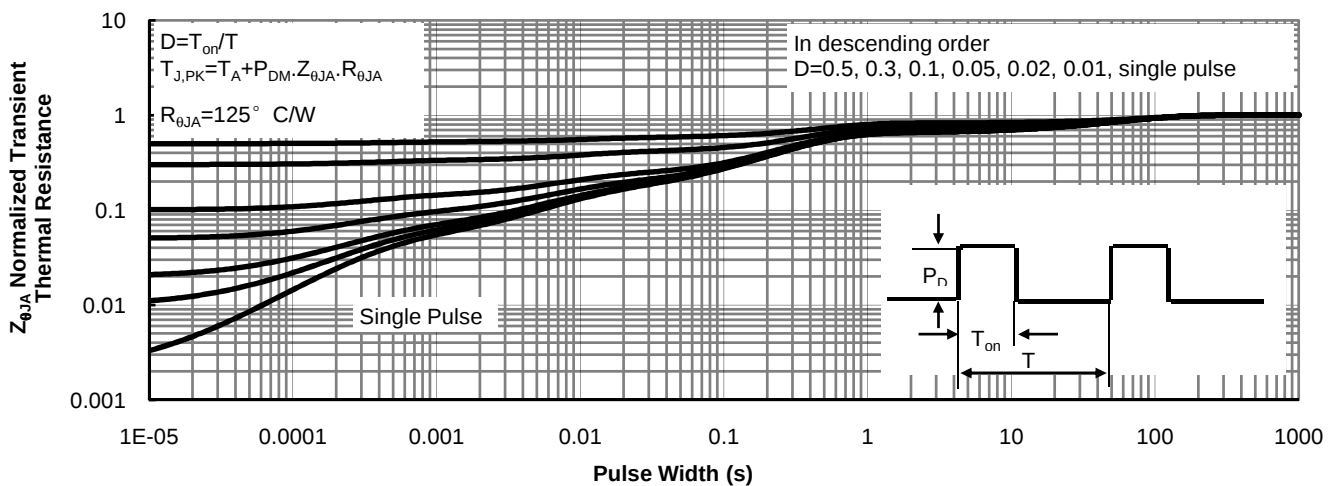
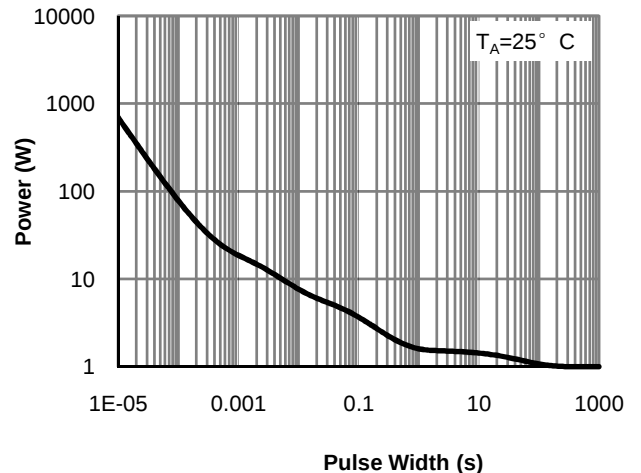
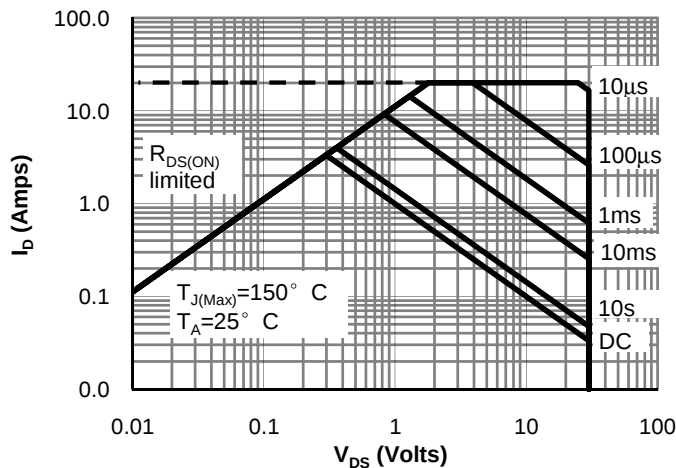
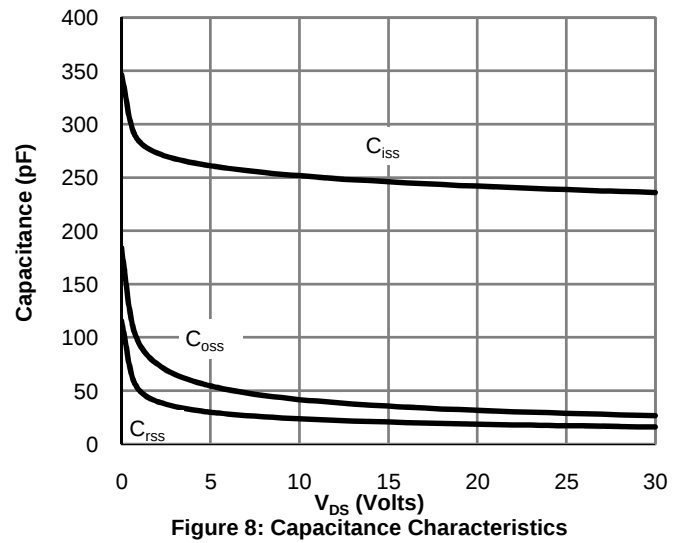
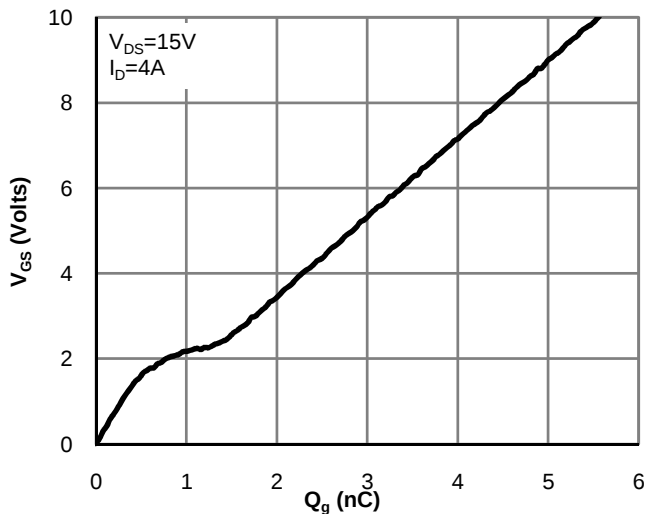
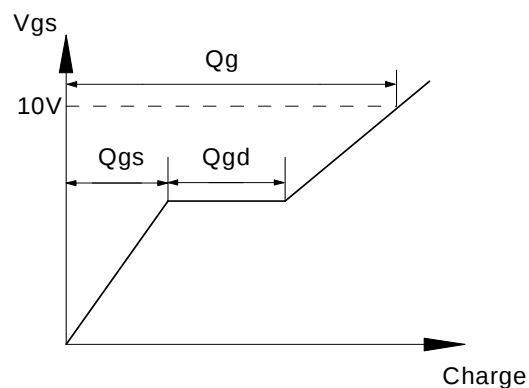
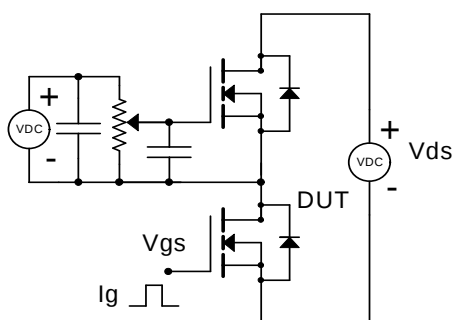


Figure 6: Body-Diode Characteristics (Note E)

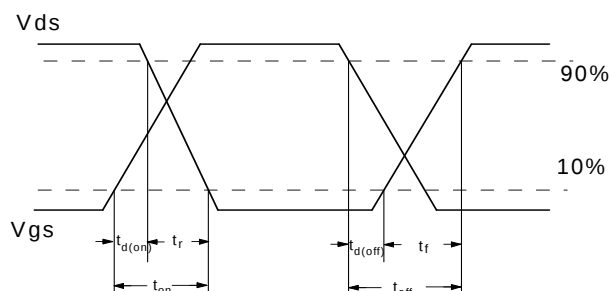
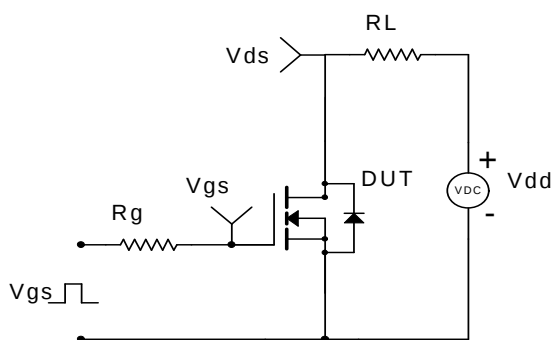


• Test circuit

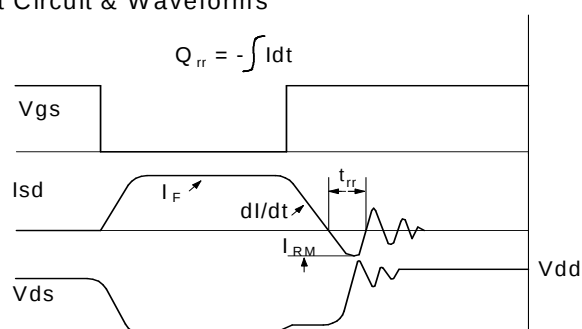
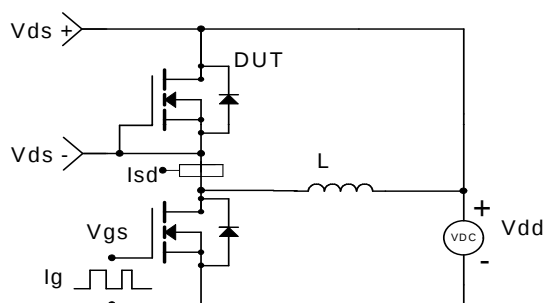
Gate Charge Test Circuit & Waveform



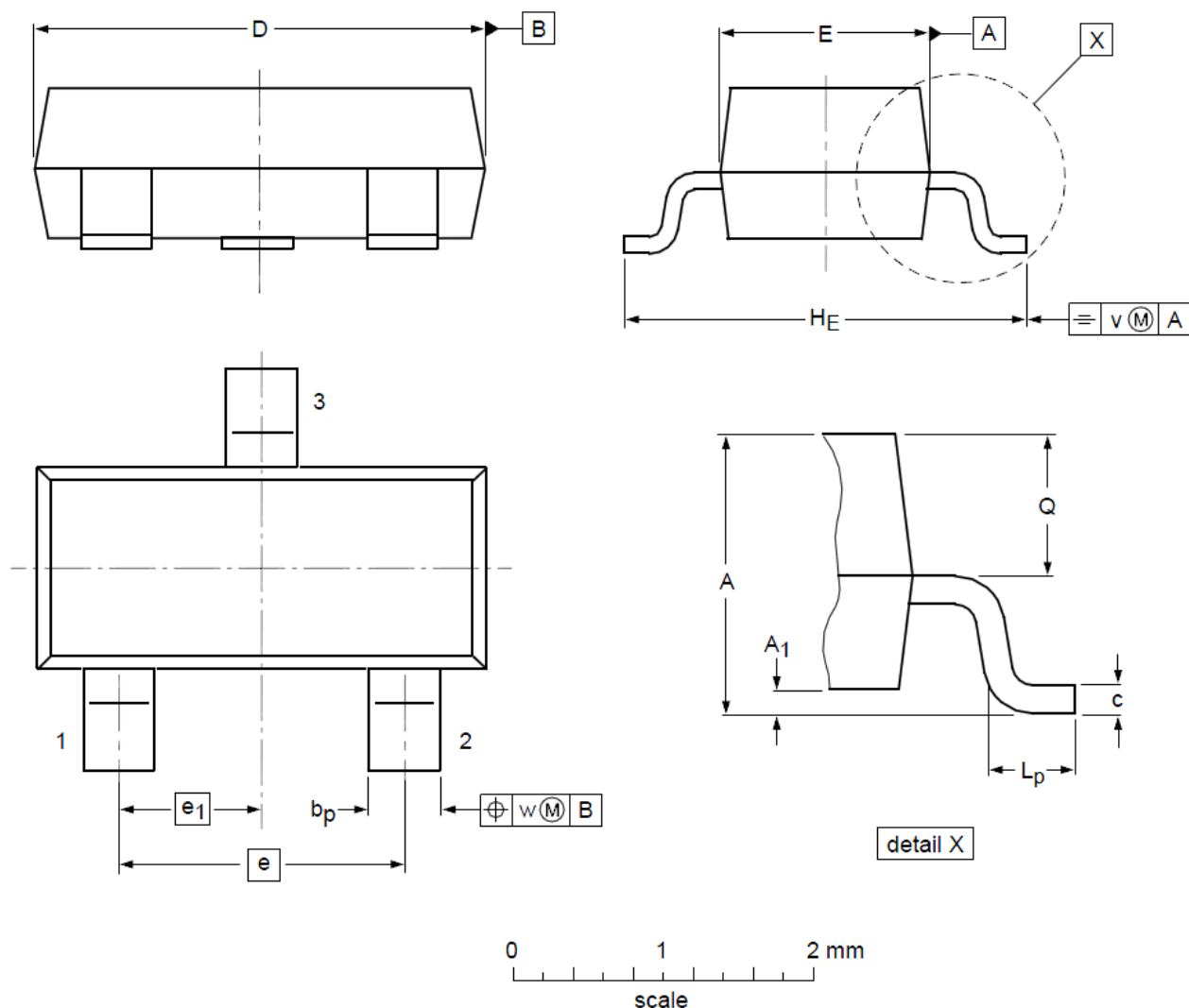
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



SOT23-3L Package Outline Dimensions



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	1.00	1.17	1.30	A ₁	0.01	0.05	0.10
b _p	0.35	0.39	0.50	c	0.10	0.20	0.26
D	2.70	2.90	3.10	E	1.30	1.58	1.70
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.50	2.78	3.00	L _p	0.20	0.32	0.60
Q	0.23	0.27	0.33	v	--	0.20	--
w	--	0.20	--				